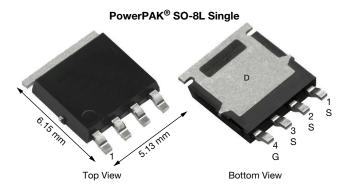
SQJ860EP

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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



| PRODUCT SUMMARY | | | | |
|---|----------------|--|--|--|
| V _{DS} (V) | 40 | | | |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$ | 0.0060 | | | |
| $R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V | 0.0073 | | | |
| I _D (A) | 60 | | | |
| Configuration | Single | | | |
| Package | PowerPAK SO-8L | | | |

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

N-Channel MOSFET

D

S



ROHS COMPLIANT HALOGEN FREE

| ABSOLUTE MAXIMUM RATING | S (T _C = 25 °C, unless | s otherwise noted | l) | | |
|---|--|-----------------------------------|-------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | 40 | V | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | |
| Continuous Drain Current | T _C = 25 °C ^a | - I _D | 60 | | |
| | T _C = 125 °C | | 36 | | |
| Continuous Source Current (Diode Conduction) | | I _S | 43 | А | |
| Pulsed Drain Current ^b | | I _{DM} | 120 | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 32 | | |
| Single Pulse Avalanche Energy | L = 0.1 MH | E _{AS} | 51 | mJ | |
| Maximum Power Dissipation ^b | T _C = 25 °C | | 48 | W | |
| | T _C = 125 °C | | 16 | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C | |
| Soldering Recommendations (Peak Temperature) d, e | | - | 260 | -0 | |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-Ambient | PCB Mount ^c | R _{thJA} | 70 | °C/W | |
| Junction-to-Case (Drain) | ion-to-Case (Drain) | | 3.1 | 0/10 | |

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|------------------------|---|---|------|--------|--------|------|
| Static | | | | | • | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0, I_D = 250 \ \mu A$ | | 40 | - | - | v |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | | 1.5 | 2.0 | 2.5 | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 V$ | V _{DS} = 40 V | - | - | 1 | μA |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V, T _J = 125 °C | - | - | 50 | |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V, T _J = 175 °C | - | - | 250 | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 30 | - | - | А |
| Drain-Source On-State Resistance ^a | _ (| V _{GS} = 10 V | I _D = 10 A | - | 0.0050 | 0.0060 | Ω |
| | P | $V_{GS} = 4.5 V$ | I _D = 8 A | - | 0.0061 | 0.0073 | |
| | R _{DS(on)} | V _{GS} = 10 V | I _D = 10 A, T _J = 125 °C | - | - | 0.0099 | |
| | | V _{GS} = 10 V | I _D = 10 A, T _J = 175 °C | - | - | 0.0122 | |
| Forward Transconductance ^b | g _{fs} | V _{DS} | = 15 V, I _D = 10 A | - | 78 | - | S |
| Dynamic ^b | | | | | • | | |
| Input Capacitance | C _{iss} | | V _{DS} = 25 V, f = 1 MHz | - | 2020 | 2700 | pF |
| Output Capacitance | Coss | $V_{GS} = 0 V$ | | - | 265 | 350 | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 110 | 150 | |
| Total Gate Charge ^c | Qg | | V _{DS} = 20 V, I _D = 20 A | - | 34 | 55 | nC |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | | - | 6 | - | |
| Gate-Drain Charge ^c | Q _{gd} | | | - | 7 | - | |
| Gate Resistance | R _g | f = 1 MHz | | 1.3 | 2.7 | 4.5 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | $V_{DD} = 20 \text{ V}, \text{ R}_L = 2 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$ | | - | 10 | 20 | ns |
| Rise Time ^c | t _r | | | - | 5 | 10 | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 30 | 50 | |
| Fall Time ^c | t _f | | | - | 5 | 10 | |
| Source-Drain Diode Ratings and Charac | teristics ^b | · | | | • | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 120 | А |
| Forward Voltage | V _{SD} | $I_F = 10 \text{ A}, V_{GS} = 0$ | | - | 0.8 | 1.2 | V |
| Body diode reverse recovery time | t _{rr} | | | - | 29 | 60 | ns |
| Body diode reverse recovery charge | Q _{rr} | I _F = 5 A, di/dt = 100 A/μs | | - | 27 | 60 | nC |
| Reverse recovery fall time | t _a | | | - | 17 | - | ns |
| Reverse recovery rise time | t _b | | | - | 11 | - | |
| Body diode peak reverse recovery current | I _{RM(REC)} | | | _ | -1.8 | -4 | Α |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

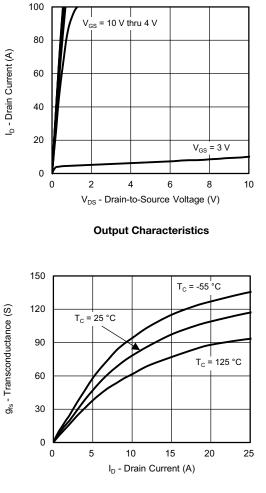
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

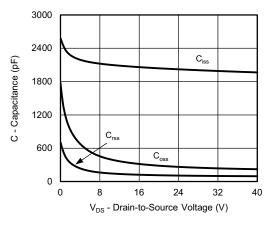


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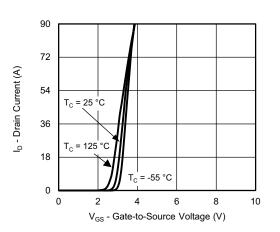
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



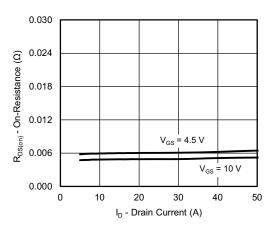
Transconductance



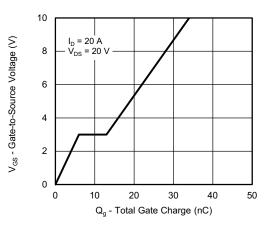




Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S16-1947-Rev. A, 26-Sep-16

3

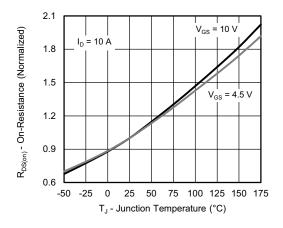
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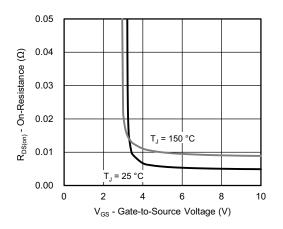


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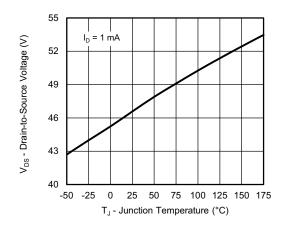
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



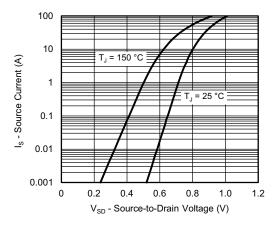
On-Resistance vs. Junction Temperature



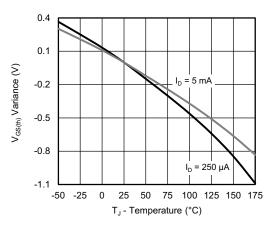
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



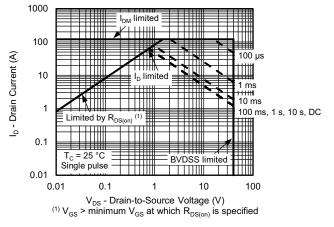
Threshold Voltage

4

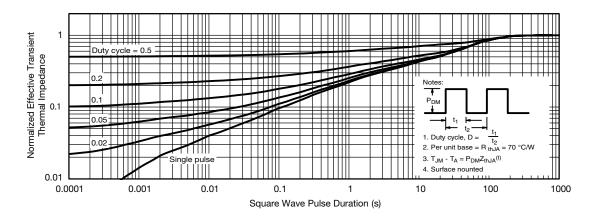


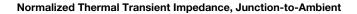
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)









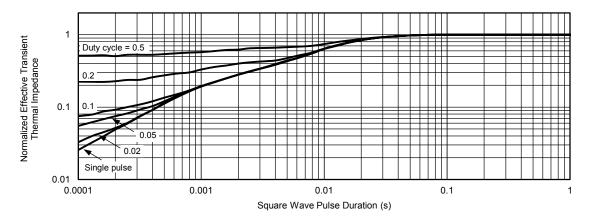


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

S16-1947-Rev. A, 26-Sep-16

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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